

## ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device comprises, in patterning of a conductive film having a grain boundary on a very thin dielectric film, a first etching step of carrying out anisotropic etching until most of the conductive film in a flat portion disappears, and a second etching step of increasing a selective ratio to the dielectric film to etch the conductive film in an unnecessary portion such that a thickness of the dielectric film provided under the grain boundary can be held to prevent oxidation species from reaching an interface with a substrate after the first etching step.